

Proposed Final Pinout for FE Chips

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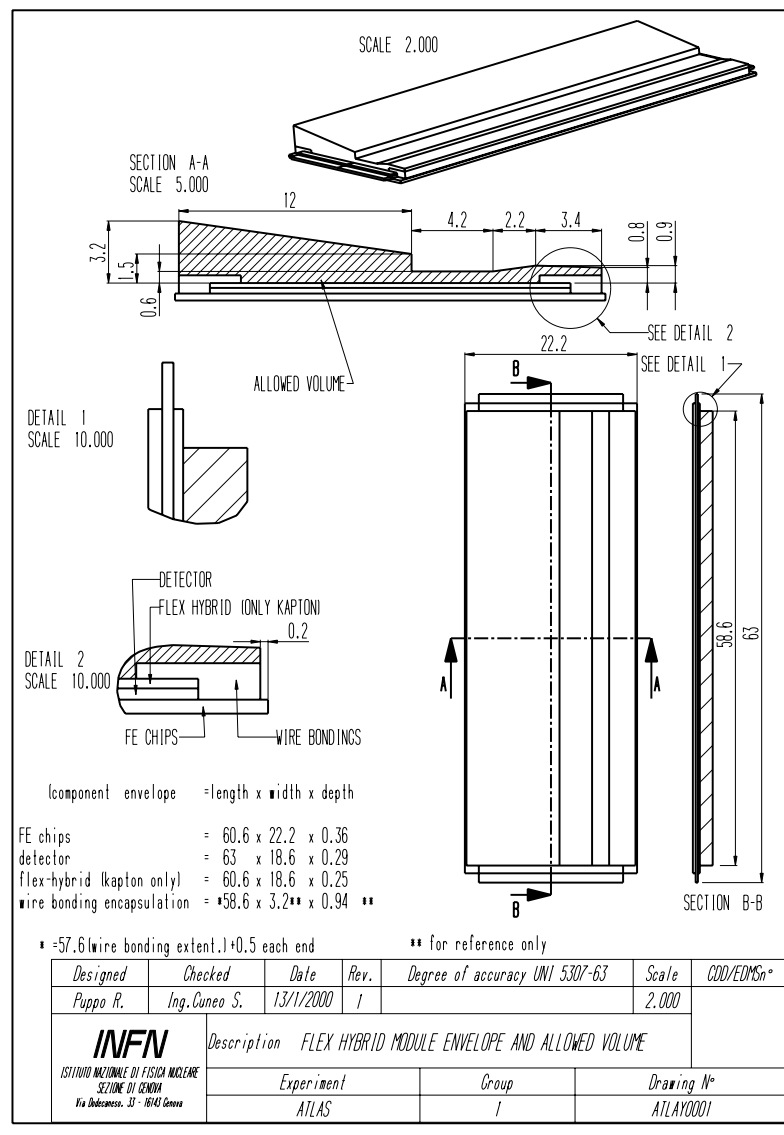
Geometry and Pinout issues:

- Need to match production pinout and geometry to proposed module envelope.

Propose final pinout, satisfying these constraints

Overview of Module Envelope

Summarize constraints on module envelope:



Constraints on FE die size:

- Present prototypes use:
7.2x(8.0+2.8)mm design size
with 0.1mm dicing zone all around:
7.4x11.0mm as-cut die size.
- Production size agreed to be same:
Provides total chip envelope in z of
 $8 \times 7.4 + 7 \times 0.2 = 60.6\text{mm}$

Constraints on FE bonding region:

- End chips have a constraint on the region which may be wire-bonded, in order to provide good Z overlap. Bonds must fit in central 57.6mm of module, meaning central 4.4mm out of the 7.4mm as-cut die width.
- If we retain the present 150μ bond-pad spacing, that corresponds to 30 bonding pads (4.35mm + pad size).

Proposed Final FE Chip Pinout (30 bonded pads):

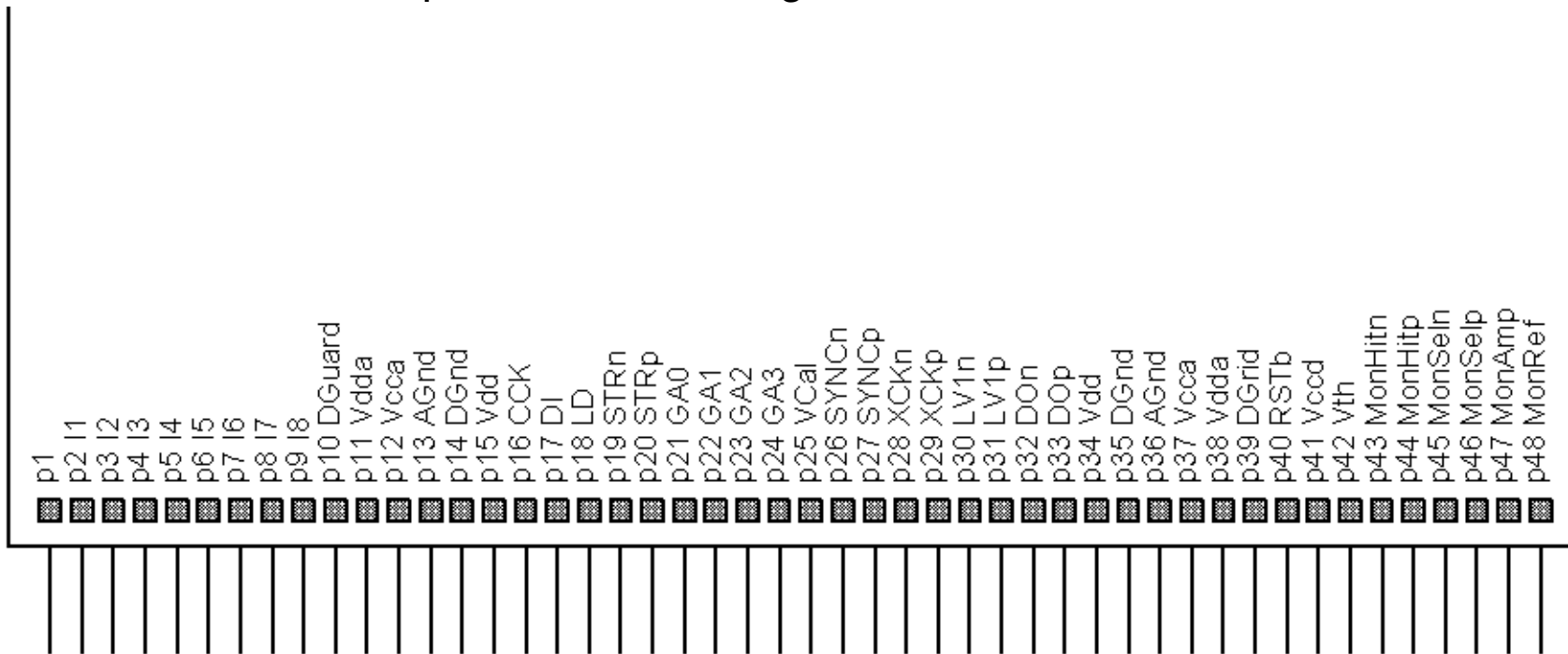
- Total of 10 power pins, positioned at 1/4 and 3/4 points in die (mirror or not ?) :
 - p11, p38 VDDA
 - p12, p37 VCCA
 - p13, p36 AGnd
 - p14, p35 DGnd
 - p15, p34 DVdd
- Total of 9 Command and Address pins:
 - p16 CCK
 - p17 DI
 - p18 LD
 - p19, p20 STRn, STRp
 - p21 - p24 GA0 - GA3
- Total of 1 analog pin (may become optional if new chopper works very well):
 - p25 VCal
- Total of 6 control pins:
 - p26, p27 SYNCn, SYNCp
 - p28, p29 XCKn, XCKp
 - p30, p31 LV1n, LV1p
- Total of 2 output pins
 - p32, p33 DOn, DOp
- Total of 2 detector pins:
 - p10 DGuard
 - p39 DGrid

To reach this, have removed 18 pads from present pinout:

- RSTb and Shield, and Analog pins (I1-I8, and VCCD/VTH)
- All monitoring pins (MonHit, MonSel, MonRef, MonAmp)
- Propose to retain most on the die, in locations compatible with present floorplans:
- Total of 1 control pin:
 - p40 RSTb
- Total of 8 current monitor pins:
 - p2 I1
 - p3 I2
 - p4 I3
 - p5 I4
 - p6 I5
 - p7 I6
 - p8 I7
 - p9 I8
- Total of 2 voltage monitor pins and 6 special monitoring pins:
 - p41 VCCD
 - p42 VTH
 - p43, p44 MonHitn, MonHitp
 - p45, p46 MonSeln, MonSelp
 - p47 MonAmp
 - p48 MonRef

Proposed Pad Geometry:

- Retain present $100\mu \times 100\mu$ pad size, with 150μ pitch
- Continue to locate pads close to the lower die edge, as for demonstrator chips.
- The present demonstrator geometry has 48 pads, with centers along a line 175μ above the bottom (referenced to the as-cut die size of $7.4 \times 11.0\text{mm}$). The first pad center is also 175μ from the vertical edge referenced to the as-cut die size.
- Propose that this pad placement would be retained, and only the central 30 pads would be used for production bonding:



Overall Chip Geometry:

